

JT0505 Gate Driver Series

28-V, +5/-7A, Single/Dual-channel, GaNs/MOSFETs/SiCs/IGBTs Gate Driver

1. Features

- Single/dual channel gate driver IC specialized to drive MOSFETs/ IGBTs / SiCs
- Compatible to drive E-mode GaNs
- VDD maximum rating up to 28V
- Wide VDD range from 4.8V to 25V
- 7-A sink, 5-A source output current enable fast switching and high efficiency
- Internal 0.8- Ω pullup and pulldown resistance
- 3.3 V, 5 V and 15 V input logic compatible
- TTL/CMOS compatible inputs
- Inputs able to sustain max VDD
- Fast propagation delay times (15-ns typical)
- Undervoltage Lockout (UVLO)
- Separate sink and source outputs for easy gate driving (JT0505M0S-T1 and JT0505G0S-T1)
- Output in phase with input
- Small form factor package (SOT23, SOP8)

JT0505 Gate Driver Series

Part Nr.	Channel	UVLO	Package
JT0505M0S-T1	1	4.5 V	SOT23-6
JT0505M0S-T2	1	4.5 V	SOT23-5
JT0505M0D-C1	2	4.5 V	SOP8
JT0505G0D-C1	2	10 V	SOP8

2. Description

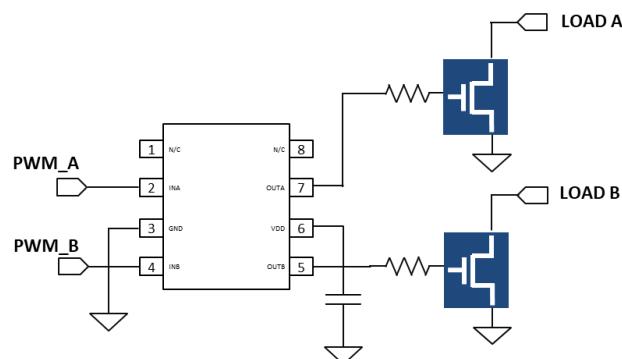
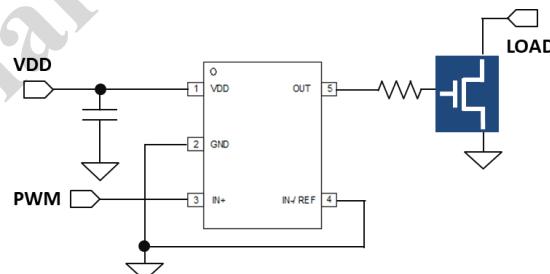
The JT0505 series gate drivers are single channel, dual channels high frequency gate driver ICs specialized to drive GaNs/ MOSFETs/ IGBTs.

The JT0505 gate drivers provide 5-A source, 7-A sink peak current capability with small propagation delay.

It offers different packages and UVLO voltage options to drive GaN/MOSFET/IGBT.

3. Application

- Switch-Mode Power Supplies (SMPS)
- PFC Systems
- DC/DC Power Converters
- Power Conversion Systems (PCS)
- Energy Storage Systems
- Solar Micro-Inverters
- Solar Optimizers



4. Table of Contents

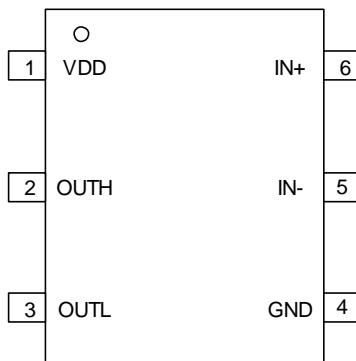
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5. Pin Configuration and Functions

5.1. JT0505M0S-T1

SOT23-6 Package

(Top view)



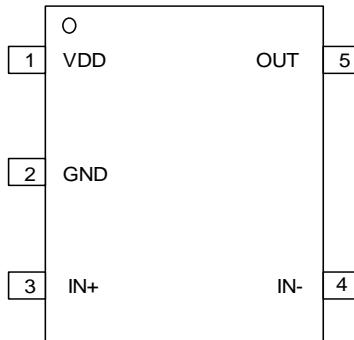
PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
VDD	1	P	Power supply
OUTH	2	O	Driver sourcing current output
OUTL	3	O	Driver sinking current output
GND	4	P	Ground
IN-	5	I	Inverting input. Connect IN- to GND in noninverting input configuration
IN+	6	I	Noninverting input. Connect IN+ to VDD in inverting input configuration

⁽¹⁾ I = Input, O = Output, P = Power, NC = Not Connected

5.2. JT0505M0S-T2

SOT23-5 Package

(Top view)



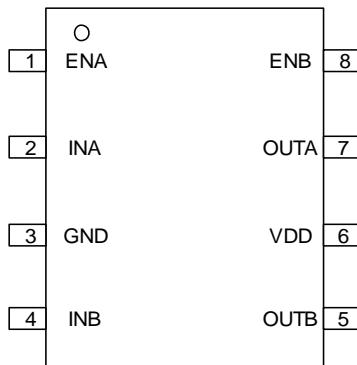
PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
VDD	1	P	Power supply
GND	2	P	Ground
IN+	3	I	Noninverting input. Connect IN- to VDD in inverting input configuration
IN-	4	I	Inverting input. Connect IN- to GND in noninverting input configuration
OUT	5	O	Driver output

(1) I = Input, O = Output, P = Power, NC = Not Connected

5.3. JT0505M0D-C1, JT0505G0D-C1

SOP8 Package

(Top view)



PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
ENA	1	I	Enable input of channel A. If ENA is high or left open, OUTA is controlled by INA. If ENA is low, OUTA is low regardless of INA.
INA	2	I	Noninverting input of channel A
GND	3	P	Ground
INB	4	I	Noninverting input of channel B
OUTB	5	O	Driver output of channel B
VDD	6	P	Power supply
OUTA	7	O	Driver output of channel A
ENB	8	I	Enable input of channel B. If ENB is high or left open, OUTB is controlled by INB. If ENB is low, OUTB is low regardless of INB.

(1) I = Input, O = Output, P = Power, NC = Not Connected

6. Specifications

6.1. Absolute maximum ratings

Parameter		Values	Unit
V _{DD}	Supply Voltage	28	V
IN+/IN-/INA/INB	Input Voltage	-0.3 to V _{DD} + 0.3	V
V _{OUT}	Output Voltage	-0.3 to V _{DD} + 0.3	V
T _J	Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-55 to +150	°C
ENA/ENB	Voltage of enable pin	-0.3 to V _{DD} + 0.3	V

6.2. ESD Rating

Parameter		Values	Unit
ESD	HBM	±1000	V
	CDM	±500	V

6.3. Thermal Information

Parameter	Values			Unit	
	SOT23-5	SOT23-6	SOP8		
R _{θJA}	Junction-to-ambient Thermal Resistance	220	220	125	°C/W
R _{θJC(top)}	Junction-to-case Thermal Resistance	100	100	70	°C/W

6.4. Recommended Operating Conditions

Parameter		MIN	NOM	MAX	Unit
V _{DD}	Supply Voltage	4.8	12	25	V
PWM	PWM Input Voltage	0	5	V _{DD}	V
T _J	Operating Junction Temperature	-40	25	125	°C

6.5. Electrical Characteristics

VDD=12V, T_j= -40°C to 125 °C unless otherwise noted.

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
SUPPLY CURRENTS						
I _{QC}	VDD quiescent current	0.35	1.09	1.2	mA	V _{IN} = 0V, VDD=12V
UNDER-VOLTAGE LOCKOUT (UVLO)						
V _{UVLO4.8+}	UVLO 4.8V turn-on Threshold ⁽³⁾	4.3	4.52	4.8	V	
V _{UVLO4.8-}	UVLO 4.8V turn-off Threshold ⁽³⁾	3.5	4.03	4.2	V	
V _{UVLO4.8H}	UVLO 4.8V Hysteresis ⁽³⁾		0.48		V	
V _{UVLO12+}	UVLO 12V turn-on Threshold ⁽⁴⁾	9.5	10	10.5	V	
V _{UVLO12-}	UVLO 12V turn-off Threshold ⁽⁴⁾	8.5	9	9.5	V	
V _{UVLO12H}	UVLO 12V Hysteresis ⁽⁴⁾		1		V	
(3) JT0505MOS-T1, JT0505MOS-T2, JT0505M0D-C1						
(4) JT0505G0D-C1						
GATE DRIVER						
I _{O+}	Peak sourcing output current		5		A	C=100nF, VDD=16V
I _{O-}	Peak sinking output current		7		A	C=100nF, VDD=16V
R _{GH}	Turn-on internal gate resistance		700		mΩ	V _{IN} =5V, I _{LO} = 500mA
R _{GL}	Turn-off internal gate resistance		500		mΩ	V _{IN} =0V, I _{LO} = -500mA
INPUTS (IN+, IN-, ENA, ENB)						
V _{IN_H}	Input signal high Threshold	1.7	1.9	2	V	
V _{IN_L}	Input signal low Threshold	1.4	1.6	1.8	V	
V _{IN_Hyst}	Input signal Hysteresis		0.2		V	
R _{IN_H}	Input pull up resistor IN- ⁽¹⁾		400		kΩ	
R _{IN_L}	Input pull down resistor IN+ ⁽²⁾		300		kΩ	
(1) Inputs with initial high logic level						
(2) Inputs with initial low logic level						

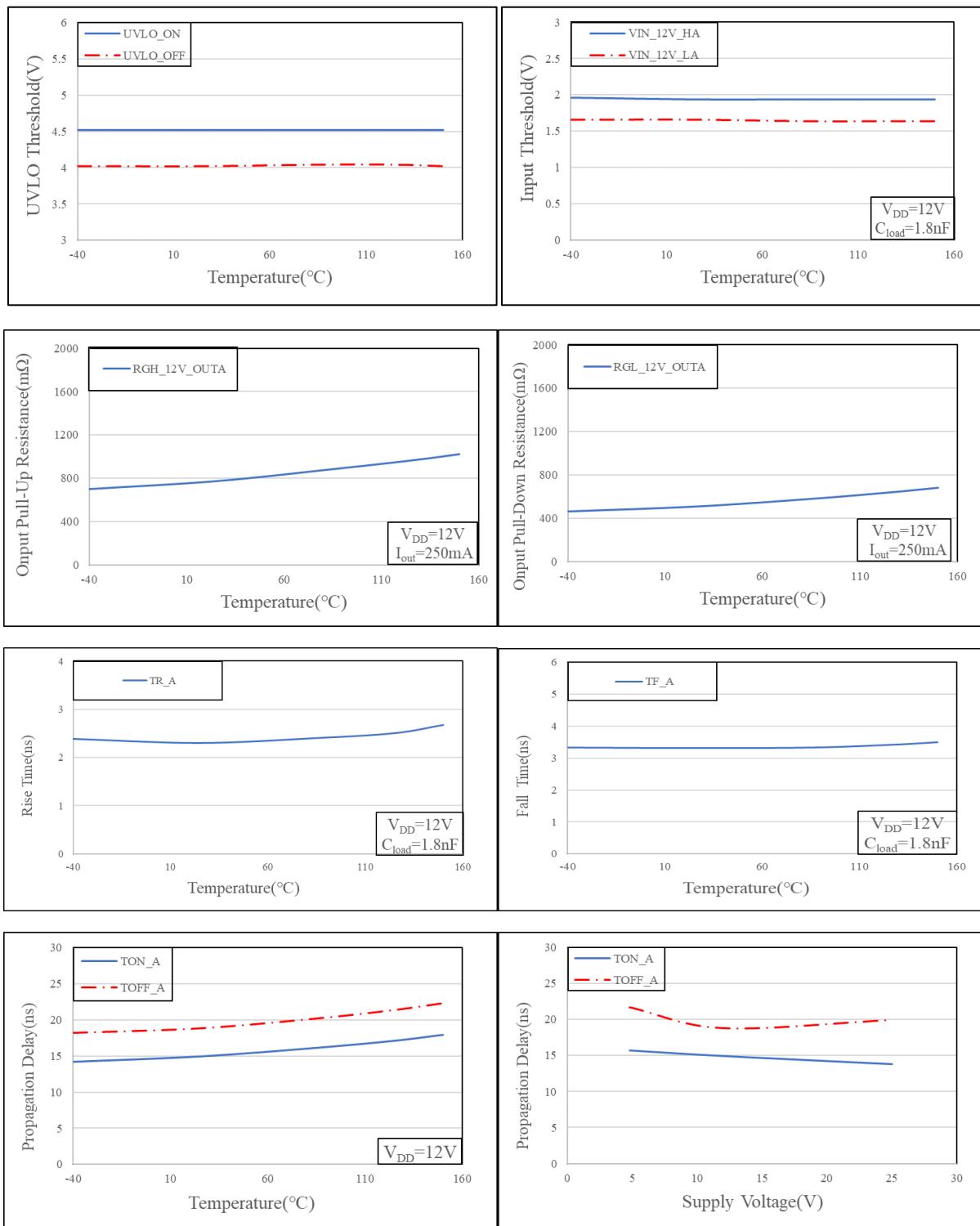
6.6. Switching Characteristics

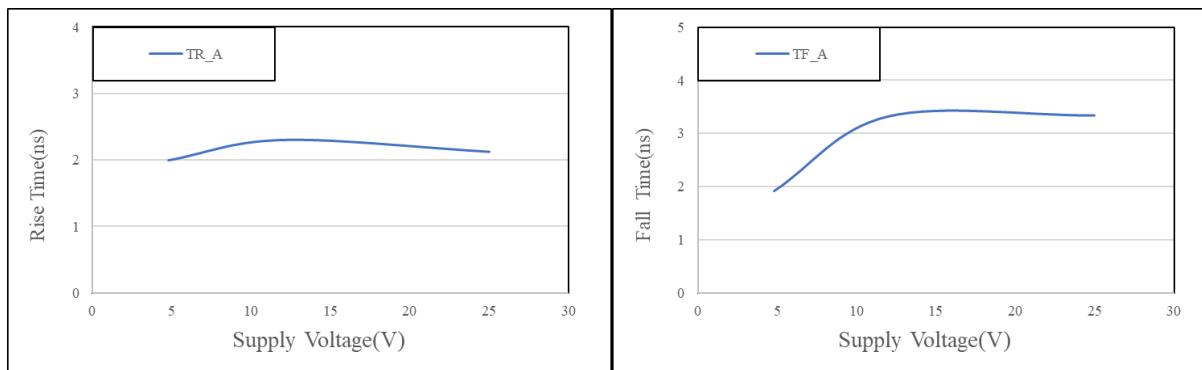
Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		

SWITCHING CHARACTERISTICS

t_{ON}	Turn-on propagation delay		15		ns	$C_{LOAD}=1.8nF, VDD=12V, 50\% \text{ to } 50\%$
t_{OFF}	Turn-off propagation delay		18		ns	$C_{LOAD}=1.8nF, VDD=12V 50\% \text{ to } 50\%$
t_R	Output rise time		2.5		ns	$C_{LOAD}=1.8nF, VDD=12V, \text{from } 10\% \text{ to } 90\%$
t_F	Output fall time		3.5		ns	$C_{LOAD}=1.8nF, VDD=12V, \text{from } 10\% \text{ to } 90\%$

6.7. Typical Characteristics





7. Functional Description

7.1. Overview

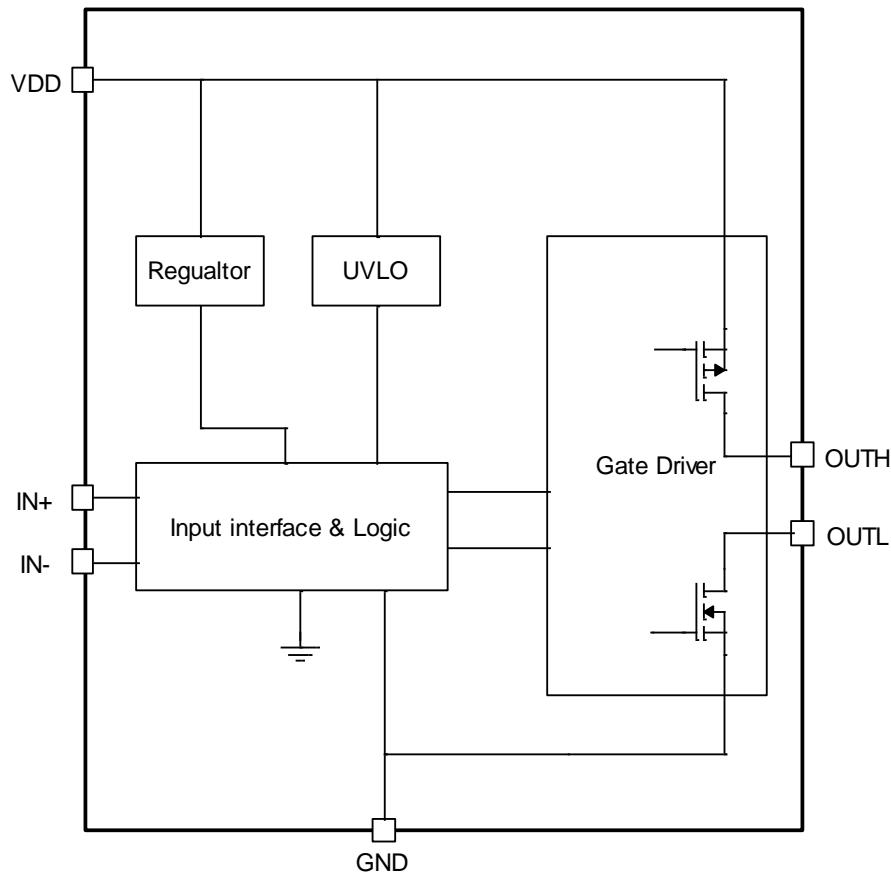
The JT0505 series gate drivers are single channel, dual channels high frequency gate driver ICs specialized to drive GaNs/ MOSFETs/ IGBTs. It offers different packages and UVLO voltage options to drive GaN/MOSFET/IGBT.

The JT0505 gate drivers provide 5-A source, 5-A sink peak current capability with small propagation delay. The split output pins, OUTH and OUTL, allow the user to apply different turn-on and turn-off resistors and control on/off slew rate independently. The OUTH and OUTL can be tied together as single output configuration.

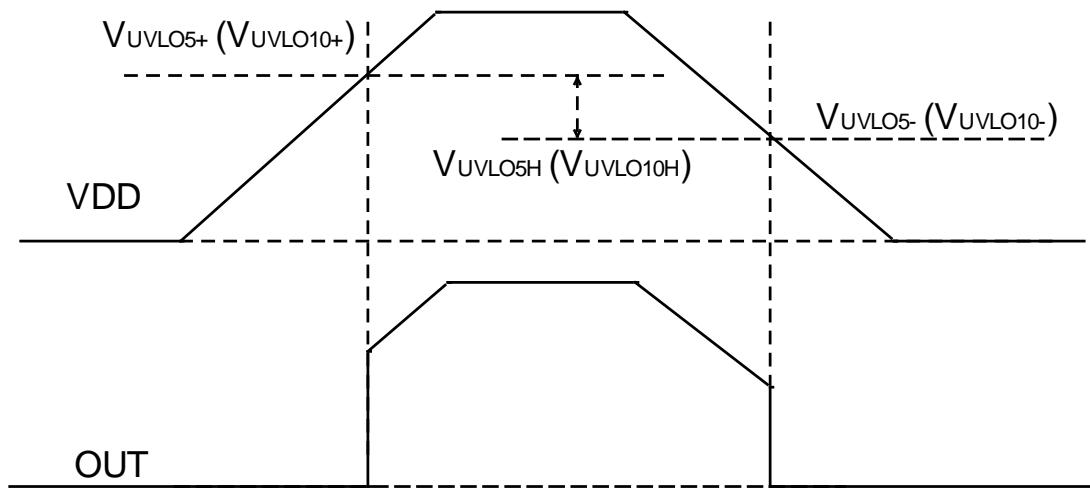
The JT0505 can operate in a wide Vdd range of 4.5-V to 25-V. The internal undervoltage lockout (UVLO) is designed to protect the power devices.

The JT0505 supports dual input with inverting (IN-) and non-inverting (IN+) configurations. The input threshold is compatible with TTL/CMOS logic.

7.2. Block Diagram (JT0505M0S-T1)



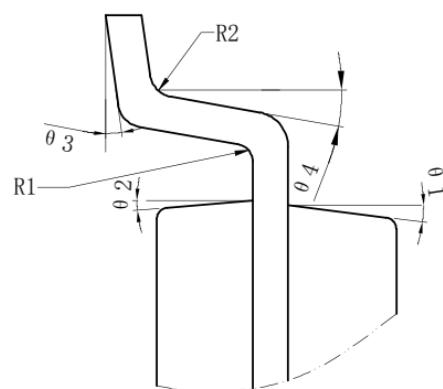
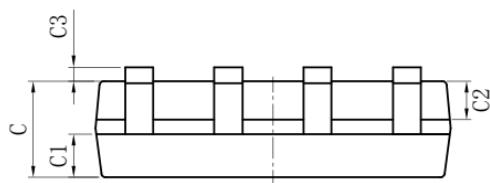
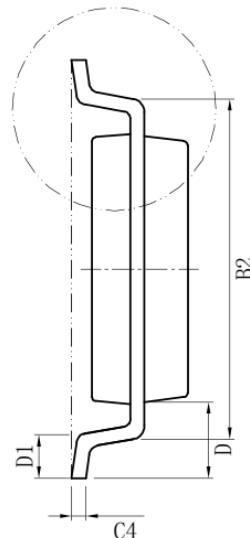
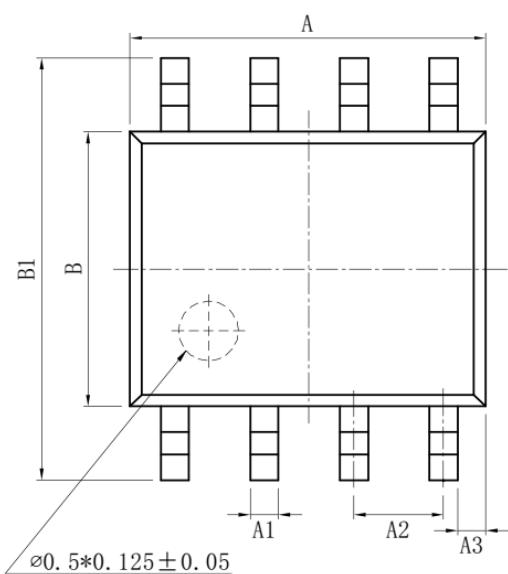
7.3. Under Voltage Lockout (UVLO)



8. Package and Bonding Information

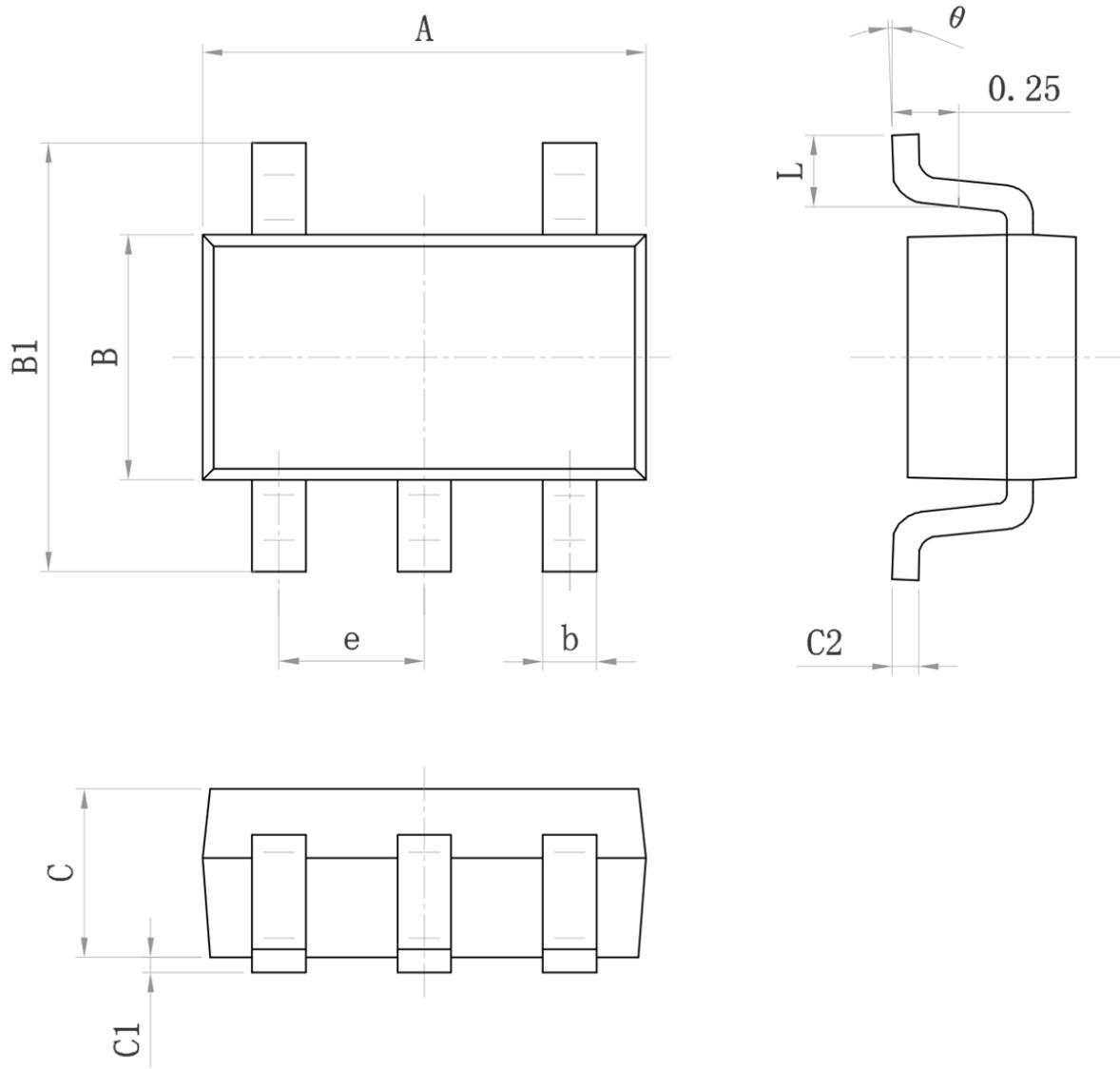
8.1. SOP8

标注 尺寸	最小 (mm)	最大 (mm)	标注 尺寸	最小 (mm)	最大 (mm)
A	4.80	5.00	C3	0.05	0.20
A1	0.356	0.456	C4	0.203	0.233
A2	1.27TYP		D	1.05TYP	
A3	0.345TYP		D1	0.40	0.80
B	3.80	4.00	R1	0.20TYP	
B1	5.80	6.20	R2	0.20TYP	
B2	5.00TYP		θ1	17° TYP4	
C	1.30	1.60	θ2	13° TYP4	
C1	0.55	0.65	θ3	0° ~ 8°	
C2	0.55	0.65	θ4	4° ~ 12°	



8.2. SOT23-5

尺寸标注	最小(mm)	最大(mm)	尺寸标注	最小(mm)	最大(mm)
A	2.82	3.02	C	1.05	1.15
e	0.95 (BSC)		C1	0.03	0.15
b	0.28	0.45	C2	0.12	0.23
B	1.50	1.70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°



8.3. SOT23-6

尺寸标注	最小(mm)	最大(mm)	尺寸标注	最小(mm)	最大(mm)
A	2.82	3.02	C	1.05	1.15
e	0.95 (BSC)		C1	0.03	0.15
b	0.28	0.45	C2	0.12	0.23
B	1.50	1.70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°

